

Feng Wei

List of Publications by Year in descending order

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26
papers

907
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687363

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1960
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#	ARTICLE	IF	CITATIONS
1	NH ₂ CH ₃ NH ₂ PbI ₃ : An Alternative Organolead Iodide Perovskite Sensitizer for Mesoscopic Solar Cells. <i>Chemistry of Materials</i> , 2014, 26, 1485-1491.	6.7	516
2	Selected-control hydrothermal synthesis and photoresponse properties of Bi ₂ S ₃ micro/nanocrystals. <i>CrystEngComm</i> , 2013, 15, 6611.	2.6	45
3	Solvothermal Growth of Single-Crystal Bismuth Sulfide Nanorods using Bismuth Particles as Source Material. <i>Crystal Growth and Design</i> , 2006, 6, 1942-1944.	3.0	41
4	Highly Transparent Dysprosium Oxide-Based RRAM With Multilayer Graphene Electrode for Low-Power Nonvolatile Memory Application. <i>IEEE Transactions on Electron Devices</i> , 2014, 61, 1388-1393.	3.0	26
5	Fabrication and electrical properties of (111) textured (Ba _{0.6} Sr _{0.4})TiO ₃ film on platinized Si substrate. <i>Applied Physics Letters</i> , 2007, 90, 042905.	3.3	25
6	Characteristics and mechanism of nano-polycrystalline La ₂ O ₃ thin film resistance switching memory. <i>Physica Status Solidi - Rapid Research Letters</i> , 2013, 7, 1005-1008.	2.4	25
7	Phase control of magnetron sputtering deposited Gd ₂ O ₃ thin films as high- ϵ gate dielectrics. <i>Journal of Rare Earths</i> , 2008, 26, 371-374.	4.8	20
8	Epitaxial La ₂ Hf ₂ O ₇ thin films on Si(001) substrates grown by pulsed laser deposition for high-k gate dielectrics. <i>Applied Physics Letters</i> , 2008, 92, .	3.3	20
9	Effect of (Ba+Sr/Ti) ratio on the dielectric properties for highly (111) oriented (Ba,Sr)TiO ₃ thin films. <i>Journal of Alloys and Compounds</i> , 2009, 475, 827-831.	5.5	18
10	Resistive switching behaviour of highly epitaxial CeO ₂ thin film for memory application. <i>Physica Status Solidi - Rapid Research Letters</i> , 2014, 8, 95-99.	2.4	18
11	High mechanical endurance RRAM based on amorphous gadolinium oxide for flexible nonvolatile memory application. <i>Journal Physics D: Applied Physics</i> , 2015, 48, 205104.	2.8	17
12	The enhancement of unipolar resistive switching behavior via an amorphous TiO _x layer formation in Dy ₂ O ₃ -based forming-free RRAM. <i>Solid-State Electronics</i> , 2013, 89, 12-16.	1.4	15
13	Twin-free (111)-oriented epitaxial Nd ₂ Hf ₂ O ₇ thin films on Ge(111) for high- ϵ dielectrics. <i>Journal Physics D: Applied Physics</i> , 2009, 42, 185301.	2.8	13
14	Effects of NH ₃ annealing on interface and electrical properties of Gd-doped HfO ₂ /Si stack. <i>Journal of Rare Earths</i> , 2013, 31, 395-399.	4.8	13
15	Cube-on-cube epitaxy of Gd ₂ O ₃ -doped HfO ₂ films on Si(100) substrates by pulse laser deposition. <i>Journal of Crystal Growth</i> , 2009, 312, 41-43.	1.5	12
16	Enhancing the efficiency of TiO ₂ -perovskite heterojunction solar cell via evaporating Cs ₂ CO ₃ on TiO ₂ . <i>Physica Status Solidi - Rapid Research Letters</i> , 2014, 8, 912-916.	2.4	12
17	Epitaxial growth and electrical properties of ultrathin La ₂ Hf ₂ O ₇ high-k gate dielectric films. <i>Applied Surface Science</i> , 2013, 283, 554-558.	6.1	11
18	Influence of the hard masks profiles on formation of nanometer Si scalloped fins arrays. <i>Microelectronic Engineering</i> , 2018, 198, 48-54.	2.4	11

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19	Epitaxial growth of HfO ₂ doped CeO ₂ thin films on Si(001) substrates for high- κ application. Applied Physics Letters, 2008, 92, 012915.	3.3	9
20	Chemical vapor deposition growth and transport properties of MoS ₂ thin layers using molybdenum and sulfur as precursors. Rare Metals, 2015, , 1.	7.1	8
21	Nonvolatile Electrochemical Metallization Memory Based on Nanocrystalline La ₂ O ₃ Solid Electrolyte Thin Film. IEEE Journal of the Electron Devices Society, 2015, 3, 254-259.	2.1	7
22	Temperature dependence of thin films growth on Si(001) substrates by pulsed laser deposition. Journal of Crystal Growth, 2008, 310, 4065-4068.	1.5	6
23	Atomic configuration of the interface between epitaxial Gd doped HfO ₂ high κ thin films and Ge (001) substrates. Journal of Applied Physics, 2012, 111, .	2.5	6
24	Interaction of Gd and N incorporation on the band structure and oxygen vacancies of HfO ₂ gate dielectric films. Physica Status Solidi (B): Basic Research, 2014, 251, 1635-1638.	1.5	6
25	Epitaxy growth and electrical properties of La ₂ Hf ₂ O ₇ thin film on Si(001) substrate by pulsed laser deposition. Journal of Physics: Conference Series, 2009, 152, 012003.	0.4	5
26	Epitaxial growth and characterization of Gd ₂ O ₃ -doped HfO ₂ film on Ge (001) substrates with zero interface layer. Journal of Rare Earths, 2013, 31, 1092-1095.	4.8	2